



Docket No. 14162

Translation
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when
3/6/03

UNITED STATES PATENT AND TRADEMARK OFFICE

VERIFICATION OF A TRANSLATION

I, Susan ANTHONY BA, ACIS,
Director of RWS Group plc, of Europa House, Marsham Way, Gerrards Cross,
Buckinghamshire, hereby England declare that:

My name and post office address are as stated below;

That the translator responsible for the attached translation is knowledgeable in the English language and in the Japanese language, and that, to the best of RWS Group plc knowledge and belief, the English translation of the marked portion of the attached Japanese document is true and complete.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Date: February 4, 2003

Signature of the director:

For and on behalf of RWS Group plc

Post Office Address :

Europa House, Marsham Way,
Gerrards Cross, Buckinghamshire,
England.

1. The present application relates to a method for the formation of metal wiring for a semiconductor device, and specifically, it relates to a method for the formation of metal wiring whereby a barrier metal film/wiring metal film is formed on the concave part formed in an insulating film, then polished by a chemical-mechanical polishing method, and claim 1, claims 8 to 12 and claims 28 to 32 of the scope of the patent claims are deemed to be easily devisable by those having common knowledge in the technical field of the invention, from technological details published in cited invention 1, "US Patent 5516346 (05.14.1996)", which details technology for the polishing of a wiring metal film (copper or the like) and a barrier metal film (TiN or the like) formed in grooves or openings by a chemical-mechanical polishing method using a polishing slurry containing silica abrasive material, oxidizing agent and fluorine-containing salt (fluoride salt) which is an inorganic salt (Patent Law 29 (2)).

2. The present application relates to a method for the formation of metal wiring for a semiconductor device, and claim 1 and claim 12 of the scope of the patent claims are for a method for the formation of metal wiring whereby a barrier metal film (metal film containing tantalum)/wiring metal film (metal film of copper or containing copper) is formed on the concave part formed in an insulating film, then polished by a chemical-mechanical polishing method, characterized in that primary polishing is performed such that the wiring metal film partly remains on the surface other than the concave part, and then secondary polishing is performed using a slurry which inhibits the wiring metal to barrier metal abrasion rate ratio to from at least 1 to no greater than 3; however, this is the same as the method disclosed in the specification and figures of patent application 2001-7007612 (06.16.2001, international application 12.16.1999,

priority claim 12.16.1998, cited invention 2) which was filed prior to the invention of the subject application, which relates to a method for forming metal wiring by forming a metal layer, formed from a tantalum-containing barrier metal film and copper, on a contact hole formed on a dielectric, and polishing the upper part of the metal layer in a first polishing process, then performing a second polishing process using a slurry having a barrier to metal selectivity of no greater than 1:1, and so claim 1 and claim 12 cannot be granted a patent under the provision of Patent Law 29 (3) (Patent Law 29 (3)).